

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-1780		PRIORITY SERIAL NO. 09/37,645	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Gurtej S. Sandhu et al.		PRIORITY FILING DATE April 17, 2001	
				PRIORITY GROUP 2813			
U.S. PATENT DOCUMENTS							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
<i>JS</i>	AA	5,320,975	6/1994	Coderbaum et al.	457	44	
<i>JS</i>	AB	5,334,851	8/1994	Pfanner et al.	257	67	
<i>JS</i>	AC	5,373,170	12/1994	Pfanner et al.	257	69	
<i>JS</i>	AD	5,411,909	5/1995	Manning et al.	437	32	
<i>JS</i>	AE	5,418,393	5,1995	Hayden	257	347	
<i>JS</i>	AF	4,945,065	7/31/90	Gregory, et al.	437	4	
<i>JS</i>	AG	5,312,108	3/18/93	Liu, et al.	437	60	
<i>JS</i>	AH	5,323,240	6/4/96	Zhang, et al.	437	21	
<i>JS</i>	AI	5,726,096	2/98	Jung	438	592	
<i>JS</i>	AJ	4,369,697	7/86	Tsu et al.			
<i>JS</i>	AK	5,665,611	9/97	Sandhu et al.	438	162	
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation Yes No
<i>JS</i>	AL	281054A1	7/90	Germany - Meade, et al.			
	AM						
	AP						
OTHER PRIOR ART (including Author, Title, Date, Portion of Page, Etc.)							
<i>JS</i>	AR	Pulback, G.P. et al., "Hydrogen Passivation of Polysilicon MOSFET's From A Plasma Nitride Source", IEEE, 1984 pp. 408-410					
<i>JS</i>	AS	Karras, T.L., "Hydrogenation of Transistors Fabricated in Polycrystalline-Silicon Films", IEEE, 1980, pp. 159-161					
<i>JS</i>	AT	Seeger, C.H. et al., "Studies of the hydrogen passivation of silicon grain boundaries", J. Appl. Phys. 52, February 1981, pp. 1030-1033					
EXAMINER		<i>hanna Schetty</i>			DATE CONSIDERED <i>10/25/04</i>		
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

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*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate	
<i>JS</i>	AA	5,605,848	2/97	Ngocarm				
<i>JS</i>	AB	5,364,803	11/93	Lay et al.				
<i>JS</i>	AC	5,830,302	11/98	Tsang et al.	428	592		
<i>JS</i>	AD	5,372,660	12/94	Fukushima et al.	427	578		
<i>JS</i>	AE	5,352,332	9/96	Tsang et al.				
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	AL							
	AM							
	AN							
	AO							
	AP							
OTHER PRIOR ART (including Author, Title, Date, Pertinent Pages, Etc.)								
<i>JS</i>	AR		Kitajima, H. et al. "Leakage Current Reduction in Sub-Micron Channel Poly-Si TFTs", Extended Abstracts - 1991 International Conference on Solid State Devices and Materials, Yokohama, 1991, pp. 174-176					
<i>JS</i>	AS		Srinada, Takashi et al. "The Role of Fluorine Termination in the Chemical Stability of HF-Treated Si Surfaces", Dept. of Electrical Engineering, Hiroshima University, Higashi-Hiroshima 724, Accepted for Publication 1990					
EXAMINER		<i>hans schult</i>			DATE CONSIDERED <i>10/25/04</i>			
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Form PRO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-1730		SERIAL NO. 09/902,177		
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Gurtej S. Sandhu et al.				
				FILING DATE July 9, 2001		PRIORITY GROUP 2813		
U.S. PATENT DOCUMENTS								
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate	
<i>JS</i>	AA	3,733,343	5/19/93	Sandhu et al.	438	163		
	AB	6,001,675	12/14/99	Sandhu et al.	438	151		
	AC	6,077,732	6/20/00	Sandhu et al.	438	153		
	AD	6,238,957	5/29/01	Sandhu et al.	438	151		
	AE							
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EXAMINER <i>hanna Schulte</i>				DATE CONSIDERED <i>10/25/04</i>				
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April 17, 2001PRIORITY GROUP
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	AA	5,605,848	2/97	Ngaoaram			
	AB	5,364,803	11/94	Lur et al.			
	AC	5,830,802	11/98	Tseng et al.	438	592	
	AD	5,372,860	12/94	Fehlner et al.	427	578	
	AE	5,552,332	9/96	Tseng et al.			
	AF	5,753,543	5/19/98	Sandhu et al.	438	163	
	AG	6,001,675	12/14/99	Sandhu et al.	438	151	
	AH	6,077,732	6/20/00	Sandhu et al.	438	158	
	AI	6,238,957	5/29/01	Sandhu et al.	438	151	
	AJ						
	AK						

FOREIGN PATENT DOCUMENTS

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	AL							
	AM							
	AN							
	AO							
	AP							

OTHER PRIOR ART (including Author, Title, Date, Pertinent Pages, Etc.)

	AR		Kitajima, H. et al., "Leakage Current Reduction in Sub-Micron Channel Poly-Si TFTs", Extended Abstract - 1991 International Conference on Solid State Devices and Materials, Yokohama, 1991, pp. 174-176					
	AS		Sunada, Takeshi et al., "The Role of Fluorine Termination in the Chemical Stability of HF-Treated Si Surfaces", Dept. of Electrical Engineering, Hiroshima University, Higashi-Hiroshima 734. Accepted for Publication 1990					

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